1.5±0.1

'n

0.4±0.04

1: Emitter 2: Collector 3: Base MiniP3 Type Package

max 0.4

 $4.0^{+0.25}_{-0.20}$ 2.5±0.1

4.5±0.1

 $.6 \pm 0.2$ 

2

0.4±0

1.5±0.1

ŀŀ

0.5±0.08

Unit: mm

## 2SB1614 Silicon PNP epitaxial planer type

For low-frequency amplification

## Features

- Large collector power dissipation P<sub>C</sub>
- Low collector to emitter saturation voltage  $V_{CE(sat)}$
- Mini power type package, allowing downsizing and thinning of the equipment and automatic insertion through the tape packing

	Absolute	Maximum	Ratings	$T_{\circ} = 25^{\circ}C$
_	/ 10001010	maximu	i iainige	1a 20 0

							45
Parameter	Symbol	Rating	Unit		3.0±0.15	┛┓╩╢	 
Collector to base voltage	V <sub>CBO</sub>	-20	V		3.0±0.15		П
Collector to emitter voltage	V <sub>CEO</sub>	-20	V				
Emitter to base voltage	V <sub>EBO</sub>	-5	V			d	$\langle \cdot \rangle$
Peak collector current	I <sub>CP</sub>	-2.4	A			¢O <sub>N</sub>	1ini
Collector current	Ι <sub>C</sub>	-2	А	Marking S	Symbol	· 2K	+
Collector power dissipation *	Collector power dissipation * $P_c$ 1 W					)	
Junction temperature	Tj	150	°C		à c	11	
Storage temperature	T <sub>stg</sub>	-55 to +150	°C	J.	. Ye	)	
Note) *: Printed circuit board con area: 1.0 Cm <sup>2</sup> or more, to Electrical Characterist	chickness: 1.7	mm	ing	Marking S 2001	_ <u>_</u>		
Parameter	Symt	lool	Conditi	ôns	Min	Тур	N
Collector cutoff current	I <sub>CBC</sub>		$-7 \text{ V}, \text{I}_{\text{B}} = 0$				-
Collector to base voltage	V <sub>CB</sub>	$_{\rm O}$ $I_{\rm C} = -$	$10 \mu A, I_E = 0$		-20		
Collector to emitter voltage	V <sub>CEC</sub>	$I_{\rm C} = 2$	$I_{\rm mA}, I_{\rm B} = 0$		-20		

## Electrical Characteristics T<sub>a</sub> = $25^{\circ}C \pm 3^{\circ}C$

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector cutoff current	I <sub>CBO</sub>	$V_{CB} = -7 V, T_{B} = 0$			- 0.1	μΑ
Collector to base voltage	V <sub>CBO</sub>	$I_{\rm C} = -10$ µA, $I_{\rm E} = 0$	-20			V
Collector to emitter voltage	V <sub>CEO</sub>	$I_{\rm C} = 71 \mathrm{mA}, I_{\rm B} = 0$	-20			V
Emitter to base voltage	VEBO	$I_{\rm E} = -10 \ \mu A, \ I_{\rm C} = 0$	-5			V
Forward current transfer ratio	h <sub>FE</sub>	$V_{CE} = -2 \text{ V}, \text{ I}_{C} = 200 \text{ mA}$	200		800	
Collector to emitter saturation voltage	V <sub>CE(sat)</sub>	$I_{\rm C} = -1$ A, $I_{\rm B} = -20$ mA		- 0.15	- 0.25	V
Collector output capacitance	C <sub>ob</sub>	$V_{CB} = -6 V, I_E = 0, f = 1 MHz$		68		pF
Transition frequency	f <sub>T</sub>	$V_{CB} = -6 \text{ V}, I_E = 50 \text{ mA}, f = 200 \text{ MHz}$		60		MHz

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